## M56733AFP

## 3-Phase Brushless Motor Driver

## Description

The M56733AFP is a semiconductor integrated circuit designed as a single-chip controller for FDD spindle motors. It incorporates a power amplifier, Hall amplifier, FG amplifier, oscillator, and speed discriminator, along with various protective circuits. Control of switching between three speeds by the single MOD pin gives this IC the edge for use in compact systems.

## Features

- Digital servo provides high precision, good stability, and freedom from the need for adjustment.
- A single pin controls switching between three speed. $\bullet \bullet$ MOD
- Two enable signals. $\bullet \bullet$ EN, $\overline{\mathrm{EN}}$
- $\mathrm{I}_{\mathrm{O} \text { (peak) }}=1.0 \mathrm{~A}$
- Low-capacitance damping capacitor


## Applications

- FDD spindle motors (5 inches)


## Recommended Operating Conditions

- Power-supply voltage: 10.8 (min.) to 13.2 (max.), 12.0 (typ.)
- Oscillation frequency: 492 kHz
- Maximum output current: 800 mA
- FG amplifier input signal level: 5 mVp -p or more


## Block Diagram



## Pin Configuration



## Absolute Maximum Ratings

$$
\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)
$$

| Symbol | Parameter | Test conditions | Ratings | Unit |
| :--- | :--- | :--- | :--- | :--- |
| $\mathrm{V}_{\mathrm{CC}}$ | Power-supply voltage |  | 15 | V |
| $\mathrm{I}_{\mathrm{O}}$ | Output current |  | 1.0 | A |
| $\mathrm{~V}_{\mathrm{HD}}$ | Hall amplifier differential input <br> voltages | Between pins 21 and 22, 23 <br> and 24, and 32 and 3 | 5 | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Voltage applied to pins | $6,13,21$ to $24,32,33$ <br> (pin numbers) | 0 to Vcc | V |
| $\mathrm{f}_{\mathrm{IN}}$ | Clock frequency |  | 1000 | kHz |
| Pt | Allowable dissipation | Infinite heat sink | 4.5 | A |
| $\mathrm{~K} \theta$ | Thermal derating range | Infinite heat sink | 27.8 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Tj | Junction temperature |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| Topr | Ambient operating temperature |  | -20 to 75 | ${ }^{\circ} \mathrm{C}$ |
| Tstg | Storage temperature | -40 to 125 | ${ }^{\circ} \mathrm{C}$ |  |

## Characteristic curves



## Electrical Characteristics

| Symbol | Parameter | Test conditions | Limits |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min | Typ | Max |  |
| Icch | Circuit Current | When the circuit is switched on. Excludes the injector current. | 9 | 18 | 28 | mA |
| ICCL | Circuit Current | When only the minimal circuit is switched on. | - | - | 300 | $\mu \mathrm{A}$ |
| $\mathrm{l}_{1 \times} \mathrm{HA}$ | Current input to the Hall amplifier |  | - | 0.4 | 4.0 | $\mu \mathrm{A}$ |
| $\mathrm{V}_{\mathrm{N}}$ | Voltage when the output is at the mid-phase point |  | 5.1 | 6.3 | 7.1 | V |
| $\Delta \mathrm{V}_{N}$ | Difference of voltage when the output is at the mid-phase point |  | - | - | 0.2 | V |
| Vsat | Saturation output voltage | $\mathrm{lo}=0.7 \mathrm{~A}$, sum of upper and lower transistors | - | 2.8 | 3.2 | V |
| $\mathrm{V}_{\text {TH }}$ | Control-input reference voltage | FLT-pin voltage for which motor rotates | 1.05 | 1.20 | 1.35 | V |
| Gv | Voltage gain between control input and output | Source side | 16.65 | 18.05 | 25.10 | dB |
|  |  | Sink side | 20.82 | 23.80 | 26.81 | dB |
|  |  | Source and sink sides | 26.00 | 28.00 | 30.00 | dB |
| $\Delta \mathrm{G}_{v}$ | Difference of voltage-gain between phases |  | - | - | 2 | dB |
| Vref | Error amplifier reference voltage | Intermediate level of discriminator output is measured | 2.0 | 2.2 | 2.4 | V |
| $\operatorname{lin} \cdot \mathrm{E}$ | Error amplifier input current |  | -0.2 | -0.02 |  | $\mu \mathrm{A}$ |
| $\mathrm{V}_{0} \bullet \mathrm{E}$ | Error amplifier output level | High | 2.2 | 2.5 | 3.1 | V |
|  |  | Low | 0.6 | 0.8 | 1.05 | V |
| $\mathrm{V}_{\text {CL }}$ | Current-limiting reference voltage | The RF pin voltage when voltage on the FLT pin falls below 1.5 V . No load. | 0.36 | 0.40 | 0.44 | V |
| $\mathrm{V}_{\mathrm{IN}}$ | Function- input threshold voltage | High Pins 6 and 13 | 2.5 | - | - | V |
|  |  | Low | - | - | 0.1 | V |
| 1 IN | Current input to the function-input pins | $\mathrm{V}_{1 \mathrm{~N}}=12 \mathrm{~V}, \mathrm{pin} 6$ | 500 | 700 | 1000 | V |
|  |  | $\mathrm{V}_{\text {IN }} 0 \mathrm{~V}, \operatorname{pin} 13$ | -150 | -100 | -70 | V |
| Vinj | Injector pin voltage |  | 0.6 | 0.9 | 1.5 | V |
| VoDSC | Discriminator output level | High | 4.1 | 4.8 | 5.3 | V |
|  |  | Low | 0.5 | 0.8 | 1.2 | V |
| $\Delta \mathrm{T}$ | Discriminator count error | +: Deceleration side Acceleration side fosc $=492 \mathrm{kHz}$ | -6 | 1 | 6 | $\mu \mathrm{A}$ |
| fosc | Oscillation frequency | fosc $=492 \mathrm{kHz}$ | -0.2 | - | 0.2 | \% |
| linjMAX | Injector max. operating current | fosc $=492 \mathrm{kHz}$ | 25 | - | - | mA |
| linjMIN | Injector min. operating current | fosc $=492 \mathrm{kHz}$ | - | - | 4 | mA |
| VOLFG | FG amplifier output low level (monitor) | $\mathrm{IL}=200 \mu \mathrm{~A}$ | - | 0.1 | 0.2 | V |
| I1FG | FG amplifier output pin leakage current (monitor) | When 12 V is applied | - | - | 1.0 | $\mu \mathrm{A}$ |
| IINMOD | Current input to the MOD pin | When 12 V is applied | 435 | 565 | 800 | $\mu \mathrm{A}$ |
|  |  | When 0 V is applied | -75 | -98 | -140 | $\mu \mathrm{A}$ |

## Application Example



## Package Dimensions



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